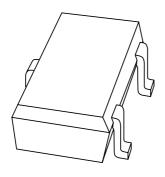
DISCRETE SEMICONDUCTORS

DATA SHEET



BC859W; BC860W PNP general purpose transistors

Product specification
Supersedes data of 1997 Jul 01
File under Discrete Semiconductors, SC04

1997 Sep 03





PNP general purpose transistors

BC859W; BC860W

FEATURES

- Low current (max. 100 mA)
- Low voltage (max. 45 V).

APPLICATIONS

 Low noise stages in tape recorders, hi-fi amplifiers and other audio-frequency equipment.

DESCRIPTION

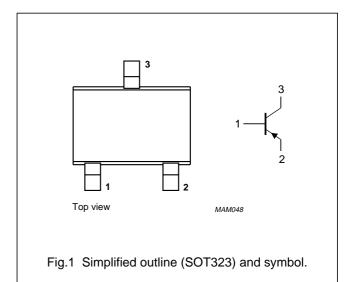
PNP transistor in a SOT323 plastic package. NPN complements: BC849W and BC850W.

MARKING

TYPE NUMBER	MARKING CODE	TYPE NUMBER	MARKING CODE
BC859W	4Dt	BC860W	4Ht
BC859AW	4At	BC860AW	4Et
BC859BW	4Bt	BC860BW	4Ft
BC859CW	4Ct	BC860CW	4Gt

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter			
	BC859W		_	-30	V
	BC860W		_	-50	V
V _{CEO}	collector-emitter voltage	open base			
	BC859W		_	-30	V
	BC860W		_	-45	V
I _{CM}	peak collector current		_	-200	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	_	200	mW
h _{FE}	DC current gain	$I_C = -2 \text{ mA}; V_{CE} = -5 \text{ V}$	125	800	
f _T	transition frequency	$I_C = -10 \text{ mA}; V_{CE} = -5 \text{ V}; f = 100 \text{ MHz}$	100	_	MHz

PNP general purpose transistors

BC859W; BC860W

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter			
	BC859W		_	-30	V
	BC860W		_	-50	V
V _{CEO}	collector-emitter voltage	open base			
	BC859W		_	-30	V
	BC860W		_	-45	V
V _{EBO}	emitter-base voltage	open collector	_	- 5	V
I _C	collector current (DC)		_	-100	mA
I _{CM}	peak collector current		_	-200	mA
I _{BM}	peak base current		_	-200	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	_	200	mW
T _{stg}	storage temperature		-65	+150	°C
T _j	junction temperature		_	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

Note

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	note 1	625	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

^{1.} Transistor mounted on an FR4 printed-circuit board.

PNP general purpose transistors

BC859W; BC860W

CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

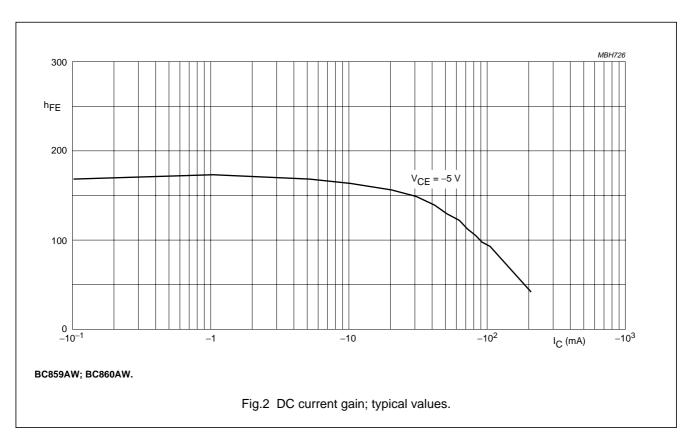
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{CBO}	collector cut-off current	$I_E = 0; V_{CB} = -30 \text{ V}$	_	_	-15	nA
		$I_E = 0$; $V_{CB} = -30 \text{ V}$; $T_j = 150 ^{\circ}\text{C}$	_	_	-4	μΑ
I _{EBO}	emitter cut-off current	I _C = 0; V _{EB} = -5 V	_	_	-100	nA
h _{FE}	DC current gain	$I_C = -2 \text{ mA}; V_{CE} = -5 \text{ V};$				
	BC859W; BC860W	see Figs 2, 3 and 4	125	_	800	
	BC859AW; BC860AW		125	-	250	
	BC859BW; BC860BW		220	_	475	
	BC859CW; BC860CW		420	_	800	
V _{CEsat}	collector-emitter saturation voltage	$I_C = -10 \text{ mA}; I_B = -0.5 \text{ mA}$	_	_	-300	mV
		$I_C = -100 \text{ mA}$; $I_B = -5 \text{ mA}$; note 1	_	_	-650	mV
V _{BE}	base-emitter voltage	$I_C = -2 \text{ mA}; V_{CE} = -5 \text{ V}$	600	_	750	mV
		$I_C = -10 \text{ mA}; V_{CE} = -5 \text{ V}$	_	_	820	mV
C _c	collector capacitance	$I_E = i_e = 0$; $V_{CB} = -10 \text{ V}$; $f = 1 \text{ MHz}$	_	_	5	pF
C _e	emitter capacitance	$I_C = i_c = 0$; $V_{EB} = -500 \text{ mV}$; $f = 1 \text{ MHz}$	_	10	_	pF
f _T	transition frequency	$I_C = -10 \text{ mA}; V_{CE} = -5 \text{ V};$ f = 100 MHz	100	_	_	MHz
F	noise figure					
	BC859W; BC860W BC859AW; BC860AW	$I_C = -200 \mu A; V_{CE} = -5 V;$ $R_S = 2 k\Omega; f = 10 Hz to 15.7 kHz$	_	_	10	dB
		$I_C = -200 \mu A; V_{CE} = -5 V;$ $R_S = 2 k\Omega; f = 1 kHz; B = 200 Hz$	_	_	10	dB
F	noise figure					
	BC859BW; BC860BW BC859CW; BC860CW	$I_C = -200 \mu A; V_{CE} = -5 V;$ $R_S = 2 k\Omega; f = 10 Hz to 15.7 kHz$	_	_	4	dB
		$I_C = -200 \mu A; V_{CE} = -5 V;$ $R_S = 2 k\Omega; f = 1 kHz; B = 200 Hz$	_	_	4	dB

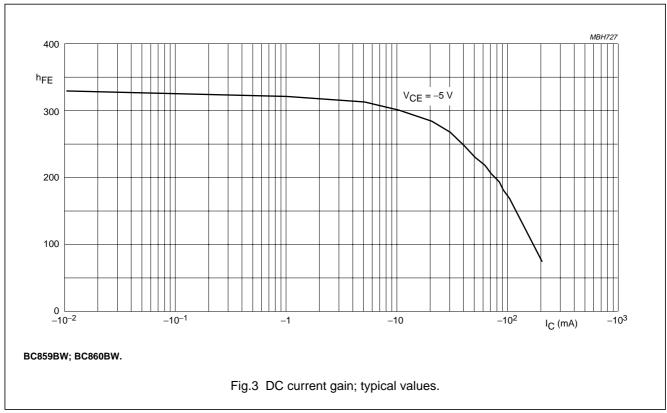
Note

1. Pulse test: $t_p \le 300~\mu s;~\delta \le 0.02.$

PNP general purpose transistors

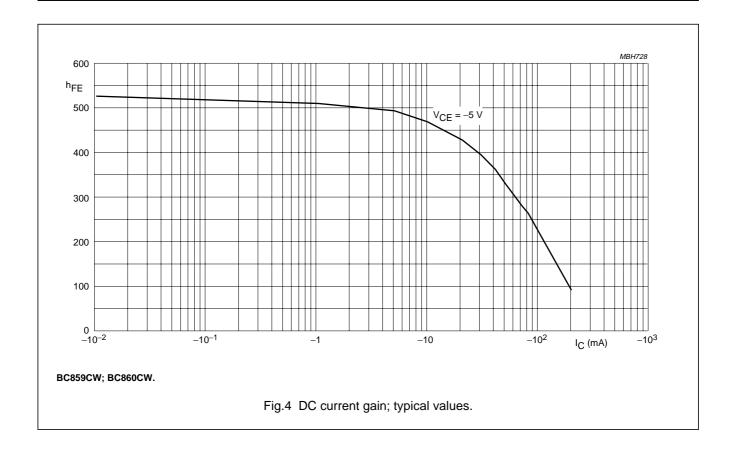
BC859W; BC860W





PNP general purpose transistors

BC859W; BC860W



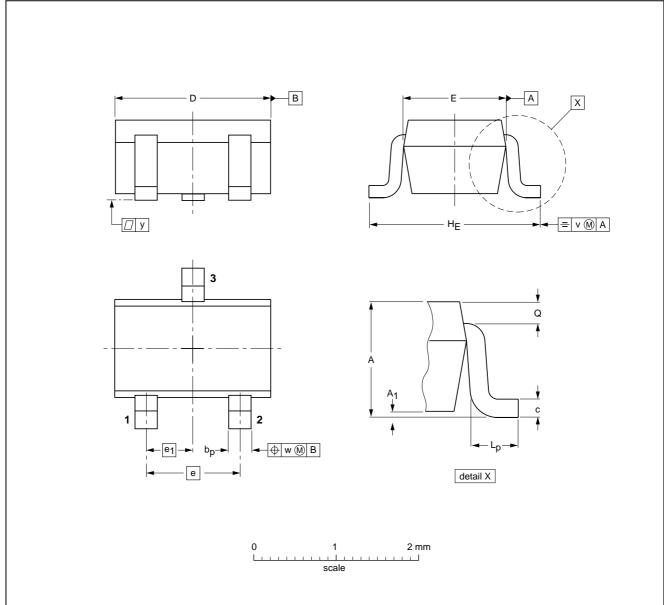
PNP general purpose transistors

BC859W; BC860W

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT323



DIMENSIONS (mm are the original dimensions)

UNIT	Α	A ₁ max	bp	С	D	E	е	e ₁	HE	Lp	Q	v	w
mm	1.1 0.8	0.1	0.4 0.3	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.23 0.13	0.2	0.2

OUTLINE		REFER	RENCES	EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	EIAJ	PROJECTION	1330E DATE
SOT323			SC-70	$ \ \ \bigoplus \big($	97-02-28

PNP general purpose transistors

BC859W; BC860W

DEFINITIONS

Data Sheet Status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	

Limiting values

Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information

Where application information is given, it is advisory and does not form part of the specification.

LIFE SUPPORT APPLICATIONS

These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips for any damages resulting from such improper use or sale.

PNP general purpose transistors

BC859W; BC860W

NOTES

PNP general purpose transistors

BC859W; BC860W

NOTES

PNP general purpose transistors

BC859W; BC860W

NOTES

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